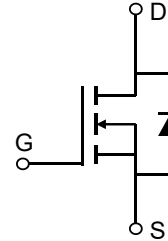


Description

Features

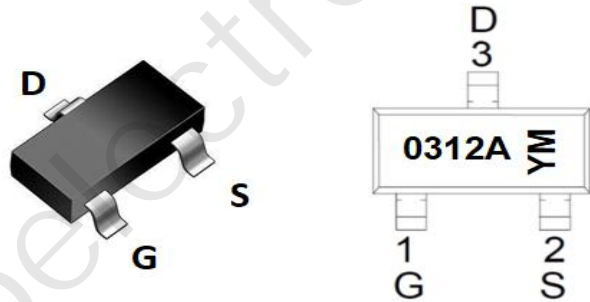
- 30V, 8A
- $R_{DS(ON)}$ Typ = 12.5mΩ @ $V_{GS} = 10V$
- $R_{DS(ON)}$ Typ = 18mΩ @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMJTL0312A	0312A	SOT-23-3L	TAPING	7"	3000	120000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	8
		$T_C = 100^\circ\text{C}$	4.8
I_{DM}	Pulsed Drain Current ⁽¹⁾	32	A
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	1.8
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾	70	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
Off Characteristics							
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	30	-	-	V	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30V, V _{GS} = 0V	-	-	1.0	μA	
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
On Characteristics							
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	2.2	V	
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 5A	-	12.5	16.3	mΩ	
		V _{GS} = 4.5V, I _D = 3A	-	18	23.4	mΩ	
Dynamic Characteristics							
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz	-	805	-	pF	
C _{oss}	Output Capacitance		-	103	-	pF	
C _{rss}	Reverse Transfer Capacitance		-	82	-	pF	
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 15V, I _D = 5A	-	16	-	nC	
Q _{gs}	Gate Source Charge		-	3.6	-	nC	
Q _{gd}	Gate Drain("Miller") Charge		-	3.4	-	nC	
Switching Characteristics							
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 15V I _D = 5A, R _{GEN} = 3Ω	-	6	-	ns	
t _r	Turn-On Rise Time		-	16	-	ns	
t _{d(off)}	Turn-Off DelayTime		-	17	-	ns	
t _f	Turn-Off Fall Time		-	5	-	ns	
Drain-Source Diode Characteristics and Max Ratings							
I _S	Maximum Continuous Drain to Source Diode Forward Current	V _{GS} = 0V, I _S = 8A	-	-	8	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A	
V _{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V	
trr	Body Diode Reverse Recovery Time		-	9.4	-	ns	
Qrr	Body Diode Reverse Recovery Charge		I _F = 5A, di/dt = 100A/us	-	3.3	-	nC
				-			

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

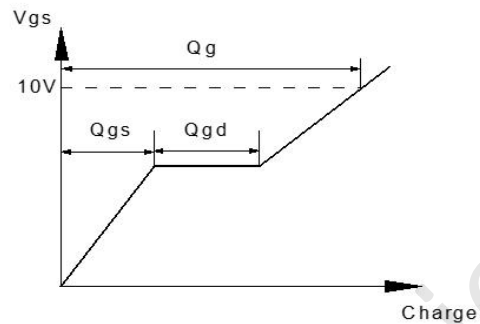
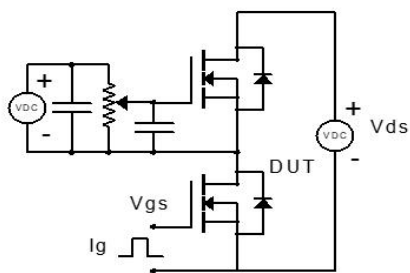


Figure 1: Gate Charge Test Circuit & Waveform

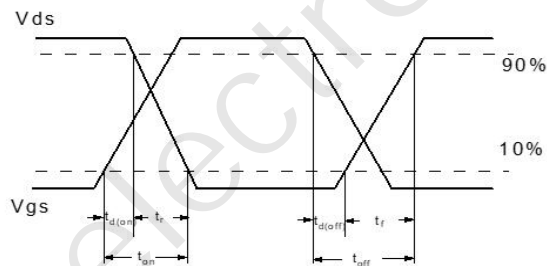
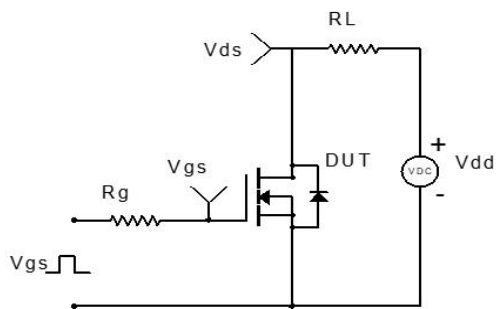


Figure 2: Resistive Switching Test Circuit & Waveform

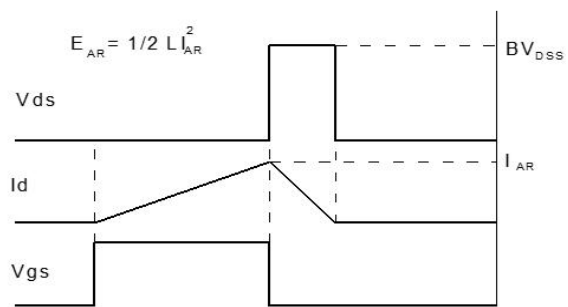
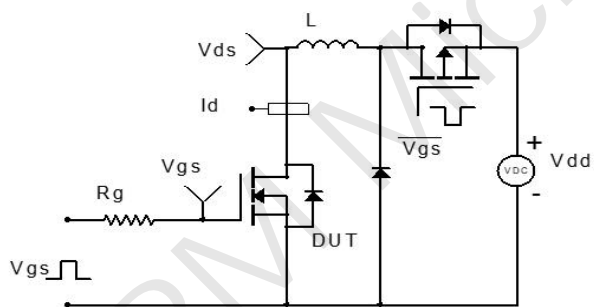


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

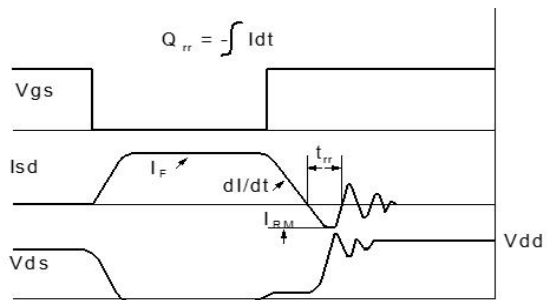
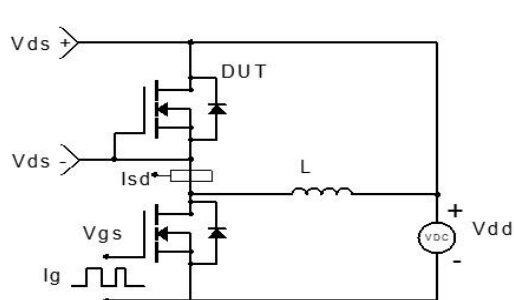
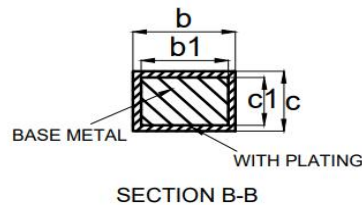
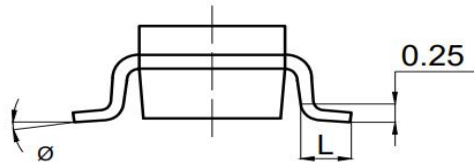
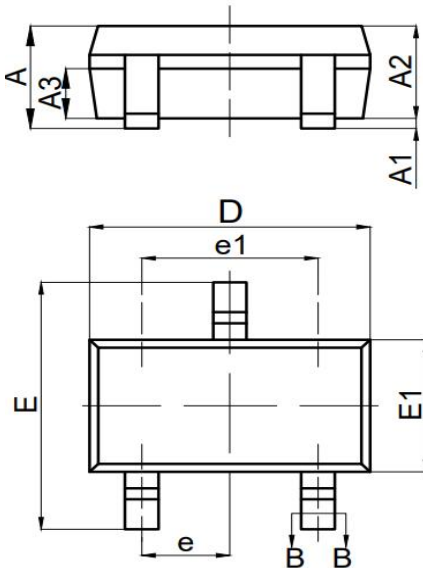


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23-3L)



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	1.25
A1	0.04	—	0.10
A2	1.00	1.10	1.20
A3	0.55	0.65	0.75
b	0.30	—	0.40
b1	0.37	0.40	0.43
c	0.11	—	0.21
c1	0.10	0.13	0.16
D	2.72	2.92	3.12
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95BSC		
e1	1.90BSC		
L	0.30	—	0.60
Ø	0	—	8°

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